

November 2013

#### **FDP030N06**

## N-Channel PowerTrench<sup>®</sup> MOSFET 60 V, 193 A, 3.2 m $\Omega$

#### **Features**

- $R_{DS(on)}$  = 2.6 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_D$  = 75 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench Technology for Extremely Low  $R_{DS(on)}$
- · High Power and Current Handling Capability
- RoHS Compliant

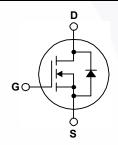
#### Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

#### **Applications**

- Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies
- · Renewable system





#### **MOSFET Maximum Ratings** T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		FDP030N06	Unit	
V <sub>DSS</sub>	Drain to Source Voltage		60	V
V <sub>GSS</sub>	Gate to Source Voltage		±20	V
		- Continuous (T <sub>C</sub> = 25°C, Silicon Limited)		
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 100°C, Silicon Limited)	136	Α
	- Continuous (T <sub>C</sub> = 25°C, Package Limited)		120	
I <sub>DM</sub>	Drain Current	- Pulsed (Note 1)	772	Α
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		1434	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns
D	Dower Dissination	$(T_C = 25^{\circ}C)$	231	W
Power Dissipation		- Derate above 25°C	1.54	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C
T <sub>L</sub>	Maximum Lead Temperature	for Soldering, 1/8" from Case for 5 Seconds	300	οС

#### **Thermal Characteristics**

Symbol	Parameter FDP030N06		Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.65	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	- C/VV

#### **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP030N06	FDP030N06	TO-220	Tube	N/A	N/A	50 units

#### **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	eteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A},  V_{GS} = 0 \text{V},  T_C = 25^{\circ}\text{C}$	60	-	-	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 1 mA, Referenced to 25°C	-	0.05	-	V/°C
1	Zero Gate Voltage Drain Current	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μА
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 48 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μΑ
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

#### **On Characteristics**

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	2.5	3.5	4.5	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 75 \text{ A}$	-	2.6	3.2	mΩ
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 75 A	-	154	-	S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 05 V V 0 V	-	7380	9815	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		1095	1455	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 1/11/12	-	415	625	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10V	V <sub>DS</sub> = 48 V, I <sub>D</sub> = 75 A,	-	116	151	nC
Q <sub>gs</sub>	Gate to Source Gate Charge	V <sub>GS</sub> = 10 V	-	40	-	nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge	(Note 4)	-	35	-	nC

#### **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time		-	39	87	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 30 \text{ V}, I_{D} = 75 \text{ A},$	-	178	366	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS}$ = 10 V, $R_G$ = 4.7 $\Omega$	-	54	118	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	-	33	76	ns

#### **Drain-Source Diode Characteristics**

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	193	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		A -	-	772	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 75 A	-	-	1.3	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 75 A,	-	46	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	50	-	nC

#### Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 0.51 mH, I  $_{AS}$  = 75 A, V  $_{DD}$  = 50 V, R  $_{G}$  = 25  $\Omega,$  starting T  $_{J}$  = 25  $^{\circ}C.$
- 3.  $I_{SD} \le 75$  A, di/dt  $\le 450$  A/ $\mu$ s,  $V_{DD} \le BV_{DSS}$ , starting  $T_J = 25^{\circ}C$ .
- 4. Essentially independent of operating temperature typical characteristics.

#### **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

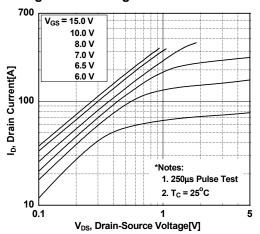


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

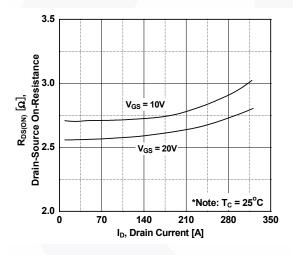


Figure 5. Capacitance Characteristics

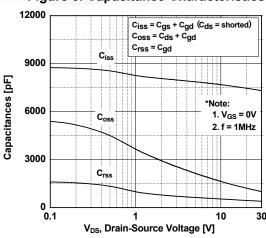


Figure 2. Transfer Characteristics

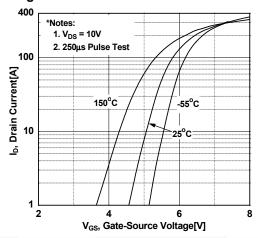
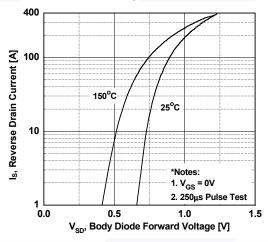
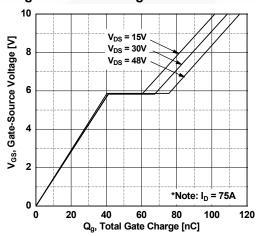


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



**Figure 6. Gate Charge Characteristics** 



#### **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

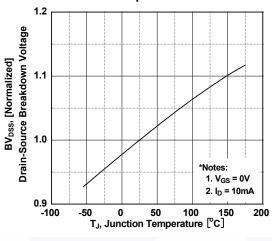


Figure 8. On-Resistance Variation vs. Temperature

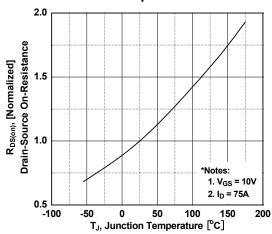


Figure 9. Maximum Safe Operating Area

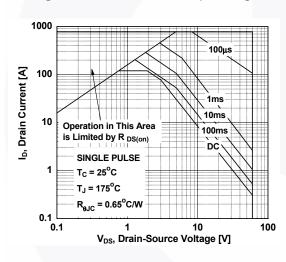


Figure 10. Maximum Drain Current vs. Case Temperature

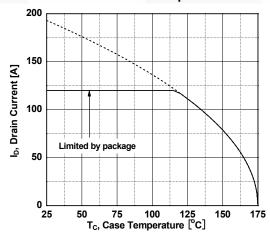
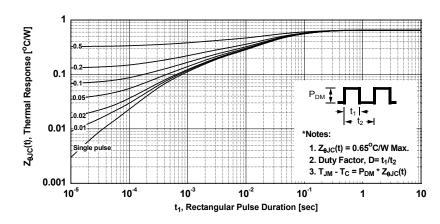


Figure 11. Transient Thermal Response Curve



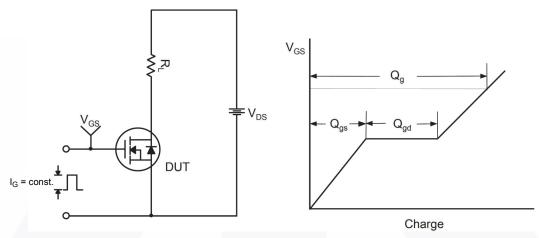


Figure 12. Gate Charge Test Circuit & Waveform

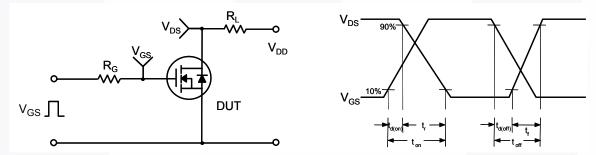


Figure 13. Resistive Switching Test Circuit & Waveforms

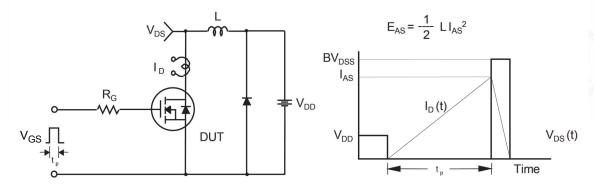


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

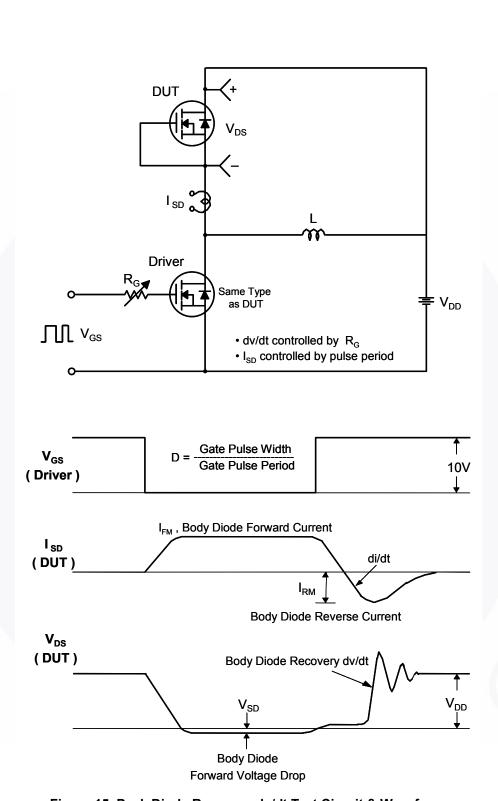


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**

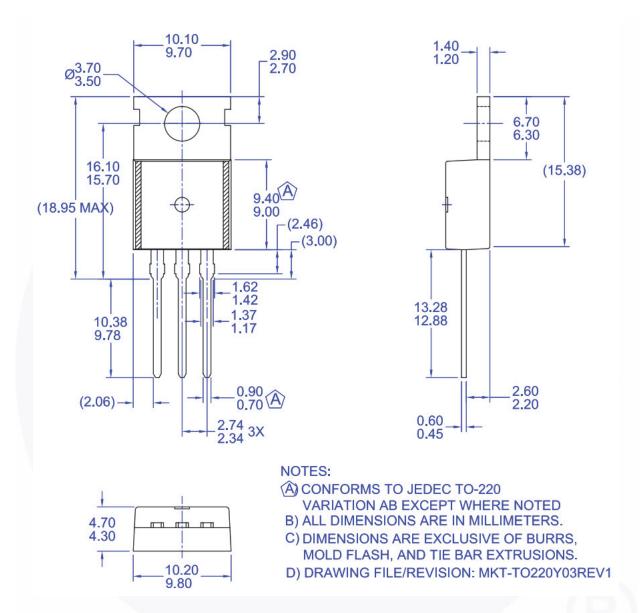


Figure 16. TO220, Molded, 3-Lead, Non Jedec Variation AB

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